

First Principles Calculations of Superconducting Critical Temperature of ThCr_2Si_2 -Type Structure

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High critical temperature (T_c) superconductor has a great potential in many industrial applications. However, discovering a compound having high T_c is still remaining a big challenge for experimental approach due to time-consuming and high cost. In this paper, we investigated the critical temperature (T_c) of several compounds of ThCr_2Si_2 -type structure (space group $I4/mmm$) since some of them had already been investigated and trusted as the potential candidates for superconductivity. First principle calculation was performed to compute the critical temperature (T_c) based on allen-dynes equation modification of McMillian formula. In order to confirm our calculation scheme, we compared our result with compounds which had been experimentally determined obtained from *NIMS* database. The result showed a very good agreement with experimental data. Based on this scheme, finally, we found ThCu_2Si_2 and ThAu_2Si_2 which were most likely to exhibit a superconductivity around 3.88 K and 4.27. Since, these compounds have not been studied experimentally, then we further investigated their electronic properties showing non-negative phonons which indicate the dynamical stability of the compounds at ambient condition. Band structure and DOS analysis showed metallic nature where the highest contributor come from d -orbital of rare-earth element and p -orbital of Si emerging a mixture of covalent, ionic and metallic bonds exists in both the compounds. Finally, we calculated the electron phonon coupling coefficient showing a quite large different (27%) leading to the increment of T_c , however, both of compounds possess three dimensional electron-like and hole-like multi-band fermi surface which is related to the phonon mediated which is still under electron-phonon mediated superconductivity.

keywords : superconductivity, ThCr_2Si_2 -type structure, ThCu_2Si_2 , ThAu_2Si_2 , critical temperature

I. INTRODUCTION

Critical temperature (T_c) is one of the most interesting phenomena in condensed matter physics for discovering the new materials which have high critical temperature. ThCr_2Si_2 -type structure ($I4/mmm$) had attracted a lot of attentions since its well-known ability for accomodating a superconducting ground state^{1,2}. This type of ternary intermetallic compounds also were observed to show as a heavy fermion behavior and novel magnetic properties.³ In this compounds, the presence of rare-earth elements such as La, Eu, Nd, Ce, etc indicated a complicated interactions due to their interactions are strongly determined by the existence of the of the correlated $4f$ electrons in the valence bands. In the other hand, $4f$ electrons do not take a significant influence in governing the

chemical bonding between atom and solid which means the s , p and d electrons mostly determine atomic volumes, crystal structures, and strength characteristic³. This interesting behaviors were caused by the $4f$ electrons are localized at respected atoms and this behavior may be changed when it is part of compounds, alloyed or changing the temperature and pressure^{2,4}. Experimental results also confirmed that the superconductivity in the d and f band metals are more complicated compared to simple metal since it may have different dependence on electron density at fermi level⁵⁻⁷. The general composition of the tetragonal ThCr_2Si_2 -type structure ($I4/mmm$) consists of stacked layers in the order of $A-[X-B_2-X]-A$ as shown in the Fig.1 where A is rare-earth or alkaline-earth metal, B is transitional metal and X comes from group 15,14, and occasionally 13 (p -block elements) formed

quasi two dimensional network called a collapsed tetragonal (cT), in other hand, at ambient temperature Ba, Sr, and Ca-based series of iron arsenides remind in the uncollapsed tetragonal structure.¹⁻⁴

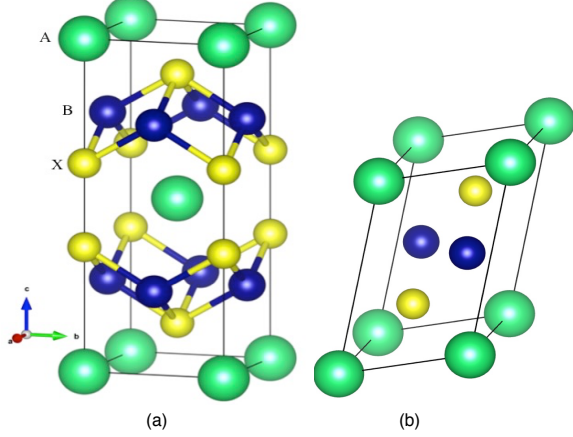


FIG. 1. (a) The conventional unit cell of AB₂X₂ with tetragonal ThCr₂Si₂-type structure and (b) primitive cell. The green, blue and yellow balls represent the A atoms is rare-earth/alkaline-earth element, B atoms is transition metal, and the X atoms come from group 15, 14, and occasionally 13 (*p*-block elements)

Superconductivity of the ThCr₂Si₂-type structures had been already much studied using experimental approach. Previous study had confirmed that CeCu₂Si₂ has a superconducting temperature at $T_c = 0.5$ K in the presence of strong Pauli paramagnetism⁸. Another experimental study found that the value of the T_c was strongly depended on the pressure given (in the range of 0.768-2.41 K) since the effective mass (m^*) at the Fermi level could be varied^{9,10}. In the another case, LaPd₂As₂ compound was also investigated.¹ The structural parameter was obtained by synchrotron X-ray diffraction (SXRD) and resistivity, magnetic susceptibility, and specific heat capacity were measured and analyzed to get the superconducting transitions temperature (T_c), moreover, the electron-phonon coupling coefficient (λ) and electronic density of state at Fermi level, $N(\epsilon_F)$, related to the T_c were calculated based on experimental and theoretical model.^{1,5} They found that the bulk superconductivity (T_c) is at 1 K. Similarly, by changing the rare-earth metal into the alkaline-earth metal, BaPd₂As₂, the superconductivity temperature increased $T_c = 3.85$ K which is higher than the other isostructure Pd-based superconductors.¹¹

In the BCS theory of superconductivity, phonons take a significant role in bringing the coupling between electrons forming Cooper pairs.¹² The aim of this work is to screen out the ThCr₂Si₂-type structure having a possible high T_c using our scheme based on *ab initio* approach and by comparing with experimental data, we can validate our scheme. Then, for the new compounds, calculation of the structural, electronics, and phonon will be performed. From the result obtained, the aver-

age phonon frequency ω_{lin} and electron-phonon coupling parameter λ for every compound were calculated. Lastly, using Allen-Dynes formulation, critical temperature of these compounds will be calculated.

II. COMPUTATIONAL METHOD

First principle calculations were performed using density functional theory (DFT) based on Kohn-Sham formulation^{13,14} implemented in Quantum Espresso package¹⁵. Plane wave basis set with 60 Ry for wave function and 600 Ry for electronic density were used. These value had been confirmed after screening its value in several compounds which always produced cutoff wave function around 40-60 Ry. This value also agree with previous studies which used 40 and 400 Ry for wave function and charge-density respectively when investigating the superconducting critical temperature of the YIr₂Si₂ and LaIr₂Si₂, and also a theoretical investigation of ThCr₂Si₂-type Pd-based superconductors^{16,17}. The accurate calculation of electron phonon coupling is very crucial problem since it needs accurate structure and the Eliashberg function of double delta over the Fermi surface which needs to be done with a high numerical accuracy¹⁸. By this understanding, all the calculations are highly depended on the functional we used. We had compared GGA and LDA functional respected to the lattice parameter of the experiment data. The lattice parameters were defined by doing relaxation of the structure minimizing the forces on the atoms with respect to lattice constants and the forces on the atoms with the coordinates. From the Table I provided, the experimental data showed a good agreement with GGA functional. Several studied also used GGA functional instead of LDA¹⁶. Noted, this is a well known problem in LDA functional which tends to overbind while GGA is underbind the structure. By using this finding, Exchange-Correlation functional was expressed using generalized gradient approximation (GGA) based on Perdew-Burke-Ernzenhof (PBE) functional, known as PBE-GGA²³. The structures optimization were done by minimizing the energy respected to the relaxation of atoms and unit cells. Phonons were calculated using 2x2x2 q-points mesh and for each q point, phonon frequencies were obtained by Fourier interpolation. In the other hand, for electronic band, DOS, and Fermi-surface, the atomic positions and charge density were obtained from structural optimization. The charge obtained from self-consistence calculation was used for non self-consistence calculation. The tetrahedron method with Blöch correction was used. The k-points were generated by Monkhorst-Pack with 16 x 16 x 8 mesh for sampling Brillouin zone in electronic DOS calculation and reciprocal unit cell in Fermi-surface calculations. The workflow for critical temperature (T_c) calculation is shown in Fig 2. First, using self consistence calculation, all parameters

will be optimized and then optimizing the compound's structure by minimizing the force on the atoms with respect to the lattice constant. The optimized structure will be used for obtaining the charge density which is used for phonon

TABLE I. Comparison of the experimental lattice constants of CeCu₂Si₂ and CeCu₂Ge₂ with GGA and LDA functional

CeCu ₂ Si ₂	GGA	LDA	Experiment ¹⁹
a (Å)	4.1287	4.0489	4.110
c (Å)	9.9880	9.7710	9.948
c/a	2.4192	2.41324	2.4204
V(Å ³)	170.2571	160.182	168.043
BaIr ₂ P ₂	GGA	LDA	Experiment ²⁰
a (Å)	3.9925	3.9256	3.9460
c (Å)	12.7550	12.4317	12.5590
c/a	3.195	3.167	3.182
V(Å ³)	203.3154	191.577	195.5551
LaFe ₂ Ge ₂	GGA	LDA	Experiment ²¹
a (Å)	4.1447	4.0553	4.11
c (Å)	10.1450	9.8917	10.581
c/a	2.447	2.439	2.574
V(Å ³)	174.2763	162.6735	178.7353
KFe ₂ As ₂	GGA	LDA	Experiment ²²
a (Å)	3.7787	3.6802	3.842
c (Å)	13.9781	13.3145	13.861
c/a	3.67	3.62	3.607
V(Å ³)	199.5873	180.323	204.6017

calculation. Phonon calculation produces the dynamical matrix for suitable uniform grid of q-vector. Dynamical matrix produced will be converted into interatomic force constants in real space. Lastly, by calculating Eliashberg function ($\alpha^2F(\omega)$), average phonon frequency ω_{ln} and electron-phonon interaction coefficient (λ), the critical temperature (T_c) of each compounds can be estimated by using allen-dynes equation modification of McMillian formula.²⁴

$$T_c = \frac{\omega_{ln}}{1.2} \exp \left[-\frac{1.04(1 + \lambda)}{\lambda - \mu^*(1 + 0.62\lambda)} \right] \quad (1)$$

where λ is the strength of electron-phonon coupling parameter, μ^* denotes the effective coulomb repulsion and ω_{ln} indicates the logarithmic average phonon frequency as shown below.

$$\omega_{ln} = \exp \left[\frac{2}{\lambda} \int_0^\infty \ln(\omega) \frac{d(\omega)}{\omega} \right] \quad (2)$$

From these equations, the main factors effect the critical temperature (T_c) are ω_{ln} and λ while for μ^* , it is well known that its value is considered physically reasonable as an adjustable parameters around 0.1 until 0.2^{12,16,24}. The electron-phonon coupling constant λ is formalized as integral of averaged coupling strength between the electrons at fermi level and the phonon energy ω ($\alpha^2F(\omega)$) described by following equation^{25–28}.

$$\lambda = 2 \int d\omega \alpha^2F(\omega)/\omega \quad (3)$$

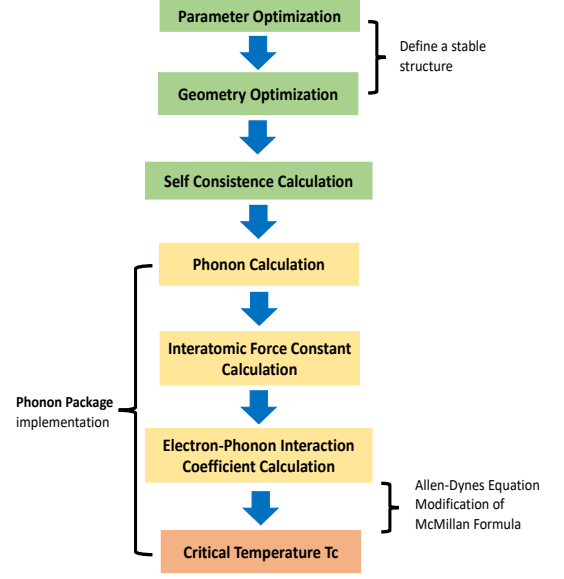


FIG. 2. Workflow scheme of the critical temperature (T_c) of ThCr₂Si₂-type structure bas on *ab initio* calculation. The critical temperature was calculated by solving the allen-dynes equation modification of McMillian formula where each parameter needed had already obtained from previous step

$$\alpha^2F(\omega) = \frac{1}{2\pi N(\epsilon_F)} \sum_{\mathbf{q}\nu} \frac{\gamma_{\mathbf{q}\nu}}{\omega_{\mathbf{q}\nu}} \delta(\omega - \omega_{\mathbf{q}\nu}) \quad (4)$$

where $N(\epsilon_F)$ is electronic density of states at the Fermi energy, $\omega_{\mathbf{q}\nu}$ is phonon frequency and linewidth ($\gamma_{\mathbf{q}\nu}$) can be expressed by fermi golden rule written as follow.

$$\gamma_{\mathbf{q}\nu} = 2\pi\omega_{\mathbf{q}\nu} \sum_{k,j'} \left| g_{\mathbf{k}+\mathbf{q},j',\mathbf{k},j}^{\mathbf{q}\nu} \right|^2 \delta(\epsilon_{\mathbf{k}j} - \epsilon_F) \delta(\epsilon_{\mathbf{k}+\mathbf{q},j'} - \epsilon_F) \quad (5)$$

The square term expresses the electron phonon matrix and $\epsilon_{\mathbf{k}j}$ is eigenvalue with k and band index j while $\epsilon_{\mathbf{k}+\mathbf{q},j'}$ indicates generated band. In the other hand, despite being determined as adjustable parameter since the detailed nature of μ^* is not well explained, parameter μ^* also can be obtained analytically from DOS at fermi level ($N(\epsilon_F)$) as follows.²⁹

$$\mu^* = 0.26 \frac{N(\epsilon_F)}{1 + N(\epsilon_F)} \quad (6)$$

It had been already understood from Equation 1 that material which has high critical temperature (T_c) has high electron-phonon interaction and average phonon frequency.

III. RESULTS

A. Comparison with experiments

We have performed our scheme based on first principle calculation for calculating around 56 critical temperature (T_c) of ThCr_2Si_2 -type structure (supplementary information). In order to compromise our calculations, we also compared it with the experimental result obtained from *NIMS* Materials Database³⁰ as follow.

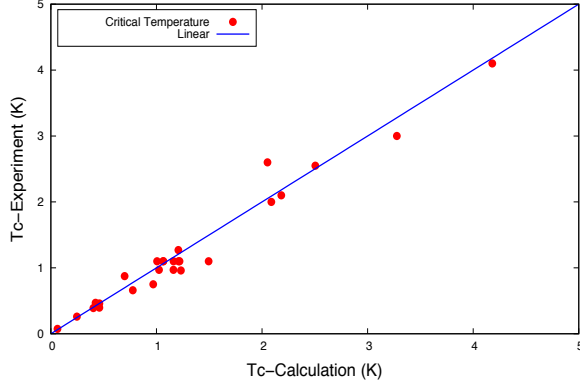


FIG. 3. Comparison critical temperature (T_c) with experimental obtained from *NIMS* Materials Database

From the Fig.3, all the critical temperatures provided by our scheme had a very good agreement with experiment indicated by linear relation. By adopting this scheme, we screen more various compounds in order to find compounds having a possible high critical temperature. Several materials also had been confirmed that LaRu_2M_2 where M is P, Si, and As was believed exhibit quite high critical temperature 4.1 K, 3.5 K, and 7.8 K.^{31–33} Some experimental studies also discovered that ThZ_2Ge_2 ($Z = \text{Pd, Rh}$) exhibited no superconductivity above 1.1 K.^{34,35} which means there are still a high possibility to discover a new superconductor compounds based on Th rare-earth element. So, from this findings, by using on our proposed method, we found compounds which exhibit a high critical temperature, ThX_2Si_2 ($X = \text{Cu, Au}$) around 3.88 K and 4.27 K. The critical temperature of these compounds have not been experimentally determined yet so they become a potential candidates providing a novel superconductivity behavior.

B. Electronic properties of ThCu_2Si_2 and ThAu_2Si_2 compounds

ThCu_2Si_2 and ThAu_2Si_2 compounds belong to ThCr_2Si_2 -type structure possessed $I4/mmm$ (139) space group in the ground state with the Wyckoff position with the Wyckoff position 2a (0,0,0) for Th (rare-earth metal), 4e (0,0,0.37856) for Si, and 4d (0,0.5,0.25) for Cu or Au (transition metal) contain-

ing ionic covalent bonding (Cu/Au)-Si inside the $(\text{Cu/Au})_2\text{Si}_2$ blocks, covalent bond between Si-Si between each layers combined with ionic bonding between $(\text{Cu/Au})_2\text{Si}_2$ and Th cations¹. The calculated lattice parameters obtained from geometry optimization showed that both of compounds have a quite similar lattice parameter, ThCu_2Si_2 ($a = 4.1131 \text{ \AA}$, $c = 9.8327 \text{ \AA}$, and $c/a = 2.39$) while for ThAu_2Si_2 ($a = 4.3421 \text{ \AA}$, $c = 10.2059 \text{ \AA}$, and $c/a = 2.35$) which is close to CeCu_2Si_2 which was experimentally calculated.¹⁹

In the other hand, in order to obtain a deep insight of the mechanism of superconductivity of ThCu_2Si_2 and ThAu_2Si_2 , the electronic properties such as projected density of states (PDOS), band structure, fermi surface, phonon dispersion and charge density different were carried out and discussed. The stability of the structure are one of the most important parameters since it affected the dynamical stability referred to the electron-phonon interaction³⁶. Then, as the first step, we analyzed the stability of the structures by performing the phonon dispersion to check whether there are the existence of negative frequencies leading to the unstable compounds. The phonon dispersion of ThCu_2Si_2 and ThAu_2Si_2 are shown in the Fig.4 respectively. It can be clearly seen that there is no negative frequencies appear in the whole high symmetry point which show that both of compounds reflect a dynamically stable at ambient condition within the harmonic approximation²⁵. A large gap also appears in the both frequency spectrum indicating there are a significant mass different between heavier atoms Th (232.038 u), Au (196.966 u), or Cu (63.546 u) and the lightest one Si (28.085 u). From this explanation, it is understandable that the difference of initial point of the 'highest' lower frequency region comes from the large mass different between Si and Au, Cu, Th. In the other hand, in the case of ThCu_2Si_2 at the higher frequency, it also exhibit a gap since Th and Cu have a large mass different while Th and Au are quite similar.

The electronic band structure of compounds were also studied since it defines some important informations to categorize whether it is metal, semiconductor or insulator. From the Fig.5 (a) and (b), both of compounds showed a metallic behaviour since in the Fermi level, some bands are overlapped (no band gap) indicating the coexistence of electron and hole pocket. So, it seems convincing that these compounds are kind of superconductor materials. Moreover, around -2 to 2 eV, the distributions of band energy are quite similar where the main contributor in the valence band comes from transition metal while in the conduction band is from rare-earth metal. This results are also supported by projected density of states (PDOS) as shown in the Fig.6. From these figures, we can see more clearly that around -2 to 2 eV, both of compounds shared almost the same electron distribution, however, the transition metal contribution in the valence band is shifted to the -6 eV in the case of ThAu_2Si_2 compared to ThCu_2Si_2 . Overall, the bands are crossing the fermi level which the main contributor to the Fermi level DOS $N(\epsilon_F)$ comes from the d orbital of Th having a strong hybridization with Si p orbital in both compounds. The calculated $N(\epsilon_F)$ showed that ThAu_2Si_2 possesses more states 3.4 states eVf.u.^{-1} compared to the ThCu_2Si_2 , 3.06 eVf.u.^{-1} having a slightly small dif-

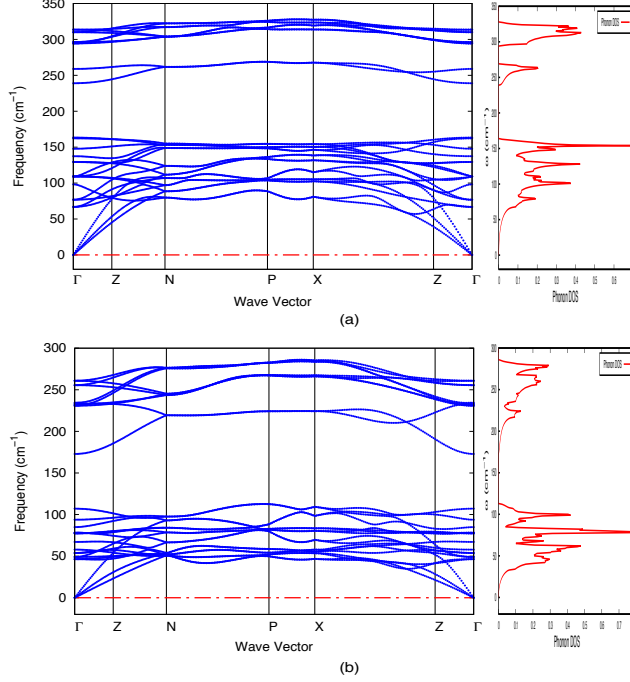


FIG. 4. Phonon dispersion along selected high symmetry point of ThCu_2Si_2 (a), and ThAu_2Si_2 (b) under $I4/mmm$ symmetry of ThCr_2Si_2 -type structure. The weighted line indicates the size of electron-phonon coupling at these q-point

ference between majority contributor Th d orbital and p orbital around $0.119 \text{ eVf.u.}^{-1}$ and 0.12 eVf.u.^{-1} respectively. In order to understand the bonding nature of these superconductor, it is important to investigate the Mulliken charge and orbital hamiltonian population analysis^{37,38}. From the Table II, it is obvious that in both of compounds, the p -block elements, Si has a negative charge while rare-earth metal and transition metal have a positive charge indicating the charge transfer from Th and Cu or Au to Si revealing the presence of some ionic features. This findings are also supported by result from three dimensional charge density in the Fig. 7, it clearly showed that there were the charge distribution overlapping between Cu/Au and Si explaining the existence of covalent bond, in contrast, no charge overlapping between rare-earth metal and also spherical like charges are also observed around Cu or Au atoms indicating the nature of ionic bond between transition metal and rare-earth metal^{39,40} which agree with the nature of metallic bond in metal case. Such this kind of interaction might be caused by the large interatomic distance between Th and Cu or Au compared to the distance between Cu or Au to Si. So, as we are expected as the nature characteristics of ThCr_2Si_2 -type structure, both of compounds possess a combination of ionic, covalent and metallic bonds. Moreover, from the integrated crystal orbital Hamiltonian population (ICOHP) value which can be considered as a standard measurement for bond strength even it does not explain ex-

plicitly the bond energy but still a good approximation.

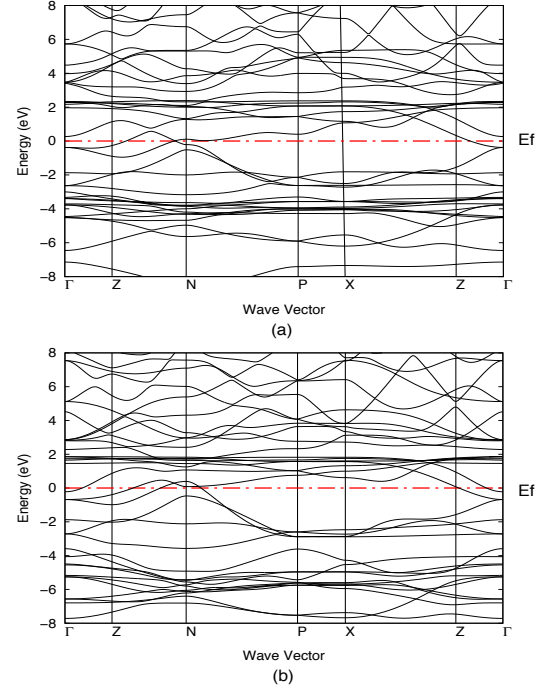


FIG. 5. The electronic band structure for (a) ThCu_2Si_2 , and (b) ThAu_2Si_2 along selected high symmetry point. The red dotted line indicates the Fermi level (E_f)

The value of -ICOHP is maximum for covalent bond when all the bonding orbitals are occupied by electrons while the antibonding orbitals are vacant inferring that the smaller value of -ICOHP the more ionic the bond (minus sign indicates the bonding)^{41,42}.

TABLE II. Mulliken and integrated orbital hamiltonian populations of ThCu_2Si_2 and ThAu_2Si_2

Compounds	Species	Charge	Bond	Bond Distance [Å]	-ICOHP [eV]
ThCu_2Si_2	Th	1.16			
	Cu	0.57	Cu-Si	2.413	-0.842
	Si	-1.14	Si-Si	2.391	-2.74
ThAu_2Si_2	Th	1.41			
	Au	0.36	Au-Si	2.581	-1.053
	Si	-1.06	Si-Si	2.311	-3.174

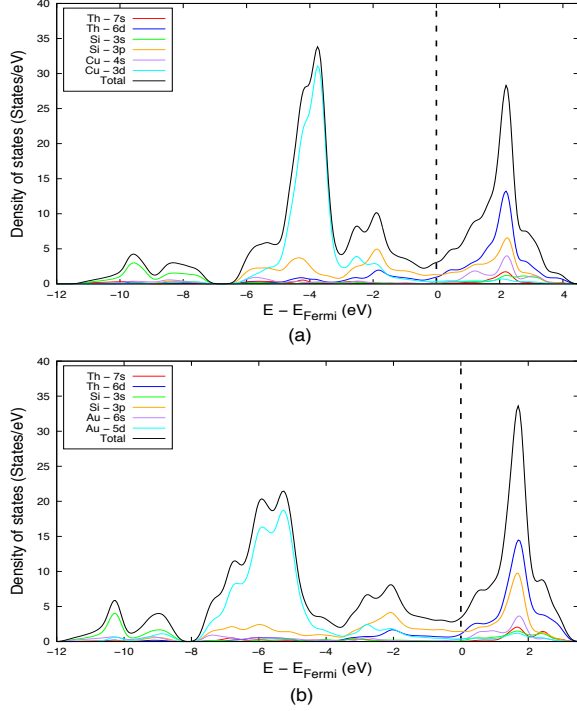


FIG. 6. Projected density of states (PDOS) of (a) ThCu_2Si_2 , and (b) ThAu_2Si_2 relative to the Fermi level denoted by horizontal dotted line

Obviously, from the Table II, the covalent bonding between transition metals with Si are weaker than Si-Si since in the case of bonding between non metal and metal, their bond is a mixture of covalent and ionic bonding called polar covalent bonding. The strength of the bondings are also strongly correlated with the bond distance and electronegativity, the measurement of the tendency of an atom to attract a bonding pair of electrons, where Au (2.4) is more electronegative than Cu (1.9) as shown as -ICOHP of the bonding's strengths between Au-Si, Cu-Si and Si-Si leading to the stability of the quasi two-dimensional (2D) network structure as we had already found in the phonon dispersion along a selected high symmetry point yielding no negative frequency mode.

C. Superconductivity properties of ThCu_2Si_2 and ThAu_2Si_2 compounds

Critical temperature (T_c) is strongly correlated with electron-phonon constant (λ) inferring a highly accurate (λ) is needed to be calculated for each compound. Generally, λ can be obtained directly by using Quantum Espresso package¹⁵ based on allen-dynes equation modification of McMillian formula. Another way is by calculating the electronic specific heat coefficient obtained from experimental (γ^{exp}) and calcu-

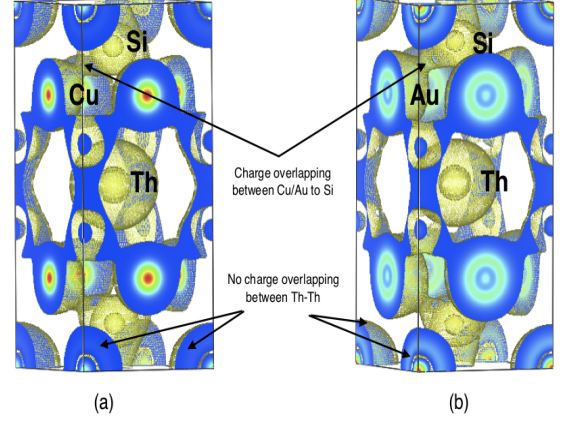


FIG. 7. Three Dimensional Charge density of ThCu_2Si_2 , and ThAu_2Si_2 . Contour level shown are between $0 \text{ e}/\text{\AA}^3$ (blue) and $0.49 \text{ e}/\text{\AA}^3$ (red)

lation (γ^{calc}) according to the relationship below.

$$\frac{\gamma^{\text{exp}}}{\gamma^{\text{calc}}} = 1 + \lambda \quad (7)$$

For (γ^{calc}), it can be simply calculated by this following equation.

$$\gamma^{\text{calc}} = \frac{\pi^2}{3} k_B^2 N(\epsilon_F) \quad (8)$$

However, since not all specific heat coefficient of compounds have been determined experimentally, sometimes, it is impossible to calculate λ based on this relation. The superconductivity properties and specific heat coefficients are summarized in the Table III below.

TABLE III. Comparison of superconducting parameters of ThCu_2Si_2 and ThAu_2Si_2 compounds

Compounds	μ^*	$N(\epsilon_F)$	ω_{ln}	λ	γ^{calc}	T_c
		[eVf.u. ⁻¹]	[K]		[mJK ⁻² mol ⁻¹]	[K]
ThCu_2Si_2	0.1	3.06	253.933	0.53	7.2	3.88
ThAu_2Si_2	0.1	3.4	90.285	0.80	8.0	4.27

In our calculation criteria for both compounds, we choose $\mu^* = 0.1$ suggested by McMillan for all transition metal and their compounds^{5,43} (values around 0.1 - 0.2 is considered physically acceptable). In BCS-type superconductor, three main factor affecting the T_c are $N(\epsilon_F)$, ω_{ln} , and λ , as we can see from the Table III, the noticeable differences between this compounds are coming from the average phonon frequency ω_{ln} and electron-phonon coupling constant λ where the value of ω_{ln} for ThCu_2Si_2 is more than 2 times larger than ThAu_2Si_2 , we predict that this result is influenced by role of transition metal in the acoustic phonon modes (see Fig. II)

leading to the noticeable different of the highest frequency in the acoustic phonon modes region. In the other hand, both of compounds have quite different λ (27% difference) since the value of λ is directly connected to the change in $N(\epsilon_F)$ in accordance with McMillan-Hopfield expression $\lambda = \frac{N(\epsilon_F)\langle I^2 \rangle}{M\langle \omega^2 \rangle}$ requiring some parameters such as average square of electron-phonon matrix element $\langle I^2 \rangle$, average square of the phonon frequency $\langle \omega^2 \rangle$, and mass M .¹² So, it is obvious that ThAu_2Si_2 has greater λ value since it has greater DOS at Fermi level (see Table III). It also had been understood that the phonon mode gives raise to a smaller ω_{ln} which brings a great contribution to λ inferring this results are still acceptable⁴⁴. Moreover, from the calculated Fermi surface (Fig.8), we found that both of compounds adopted the tetragonal ThCr_2Si_2 -type structure having three-dimensional electron-like and hole-like multi-band FS's as most of the same type compounds have^{45,46}.

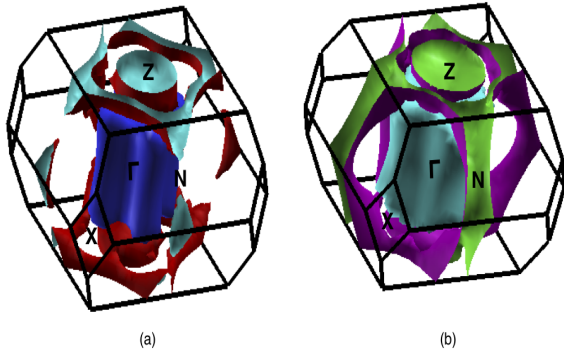


FIG. 8. Fermi surface sheets of (a) ThCu_2Si_2 , and (b) ThAu_2Si_2 within tetragonal Brillouin zone boundaries. The characters of Fermi surfaces are primarily constituted by Th 6d, Si 3p, and Cu 3d or Au 5d states

Finally, the two compounds appear to be typical of superconductors mediated by phonons (BSC-type superconductor) exhibiting a superconductivity at low temperature (however, it is high compared to another compounds having the same structure) and it is not required any special dimensionality of Fermi surface requiring possible nesting vector which can favor electron's pairscoring from different conduction band⁴⁷.

IV. CONCLUSION

In summary, we have performed our scheme to calculated several critical temperature of material which had already determined by experimental approach. The trends showed that our result had a good agreement with experimental. Using this scheme, we explored another possible compounds which has possible quite high critical temperature and we found that ThCu_2Si_2 and ThAu_2Si_2 exhibited a high critical temperature compared to another compounds, 3.88 K and 4.27 K. The absence of negative frequencies and gaps showed that the stability of compounds in ambient condition and metallic nature. In the fermi level, the majority contribution came from d -orbital

of Th having a strong hibridization with p -orbital of Si resulting in the existence of a mixture of covalent, ionic and metallic bonds. In the last, both of compounds possess three-dimensional electron-like and hole-like multi-band fermi surface which is related to the phonon mediated superconductor (BCS-type superconductor).

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Appendix A: Supplementary Data

TABLE IV. Superconducting data of several compounds of ThCr₂Si₂-type structure

Compounds	μ^*	ω_{ln} [K]	λ	T _c (Cal) [K]	T _c (Exp) [K]	Compounds	μ^*	ω_{ln} [K]	λ	T _c (Cal) [K]	T _c (Exp) [K]
LaPd ₂ As ₂	0.1	98.111	0.64	1.02	0.97	CeAu ₂ Si ₂	0.13	130.158	0.63	2.50	2.55
CeCu ₂ Si ₂	0.1	216.214	0.36	0.46	0.46	LaZn ₂ Al ₂	0.13	172.654	0.43	0.50	-
CeCu ₂ Ge ₂	0.1	147.465	0.54	2.09	2.0	LaCo ₂ B ₂	0.13	263.651	0.38	0.34	-
ThNi ₂ Si ₂	0.13	255.615	0.42	0.70	0.875	LaCu ₂ Si ₂	0.13	310.788	0.43	0.91	-
CaPd ₂ As ₂	0.18	89.785	0.68	1.21	1.27	LaFe ₂ Ge ₂	0.1	181.988	0.26	0.02	-
LaIr ₂ Si ₂	0.13	281.038	0.44	1.06	1.1	LiCu ₂ P ₂	0.1	273.598	0.45	2.19	-
LaNi ₂ P ₂	0.1	216.544	0.47	2.05	2.6	LuCu ₂ Si ₂	0.1	253.861	0.31	0.17	-
YSi ₂ Ir ₂	0.13	274.613	0.46	1.21	1.1	ThMn ₂ Si ₂	0.13	126.909	0.59	1.95	-
ThPd ₂ Ge ₂	0.16	112.237	0.63	1.49	1.1	LiCu ₂ P ₂	0.13	273.232	0.45	1.17	-
ThRh ₂ Ge ₂	0.13	172.754	0.50	1.22	1.1	CaNi ₂ Si ₂	0.13	307.447	0.37	0.29	-
SrPd ₂ Ge ₂	0.18	102.355	1.16	6.04	2.7	ZrNi ₂ Si ₂	0.13	275.167	0.36	0.19	-
CePd ₂ Si ₂	0.15	214.33	0.44	0.46	0.395	CaCu ₂ Ge ₂	0.13	101.76	0.48	0.64	-
YPd ₂ Si ₂	0.14	222.338	0.42	0.42	0.47	CaCu ₂ Si ₂	0.13	286.13	0.42	0.81	-
CeRh ₂ Si ₂	0.14	235.896	0.39	0.25	0.26	CaAg ₂ Ge ₂	0.13	177.649	0.52	1.52	-
LaPd ₂ Si ₂	0.15	143.876	0.46	0.40	0.39	LaCo ₂ Ge ₂	0.13	183.784	0.28	0.01	-
LaRh ₂ Si ₂	0.13	251.498	0.33	0.06	0.074	CaCo ₂ Ge ₂	0.13	258.216	0.19	0.001	-
LaRu ₂ P ₂	0.13	129.157	0.75	4.18	4.1	CaNi ₂ Ge ₂	0.13	141.426	0.63	2.73	-
BaNi ₂ Si ₂	0.13	251.554	0.57	3.28	3.0	CaAu ₂ Si ₂	0.13	118.548	0.68	2.84	-
YRh ₂ Si ₂	0.1	277.89	0.39	1.01	3.1	ThFe ₂ Ge ₂	0.13	206.154	0.31	0.02	-
LaRu ₂ Si ₂	0.13	221.098	0.28	0.04	3.5	LaAg ₂ Si ₂	0.1	299.071	0.33	0.33	-
BaIr ₂ P ₂	0.13	149.668	0.58	2.18	2.1	LaCo ₂ Si ₂	0.1	258.314	0.29	0.10	-
BaNi ₂ As ₂	0.13	96.987	0.96	4.80	0.68	LaFe ₂ Si ₂	0.1	226.559	0.24	0.01	-
SrNi ₂ As ₂	0.15	114.93	0.53	0.78	0.66	LaPd ₂ Ge ₂	0.13	140.455	1.25	11.73	-
YOs ₂ Si ₂	0.1	234.983	0.32	0.21	1.1	SrRh ₂ Ge ₂	0.1	207.275	0.30	0.10	-
LaRu ₂ As ₂	0.19	212.018	1.11	10.96	7.8	LaRu ₂ Ge ₂	0.13	153.636	0.33	0.18	-
LaPd ₂ P ₂	0.16	209.032	0.51	0.97	0.75	ThCu ₂ Si ₂	0.1	253.933	0.53	3.88	-
YPd ₂ P ₂	0.15	118.751	0.58	1.23	0.96	ThAu ₂ Si ₂	0.1	90.285	0.80	4.27	-
YRu ₂ Si ₂	0.13	251.94	0.29	1.16	1.1	LuNi ₂ Ge ₂	0.1	139.941	0.61	2.38	-